



TWO-WIRE AUTOMOTIVE HALL SWITCHES INTEGRATED SELF-DIAGNOSTICS

Description

The DIODES[™] AH3241Q-AH3244Q/AH3280Q-AH3282Q are high voltage, high sensitivity, two-wire Hall Effect Unipolar/Latch switch ICs with integrated self-diagnostics and automotive-compliant AEC-Q100 qualification; designed for position and proximity sensing in automotive applications, such as seat and seatbelt buckle, transmission actuator, gear position, wiper, door/trunk closure, etc.

To support a wide range of demanding applications, the AH3241Q-AH3244Q/AH3280Q-AH3282Q are optimized to operate over a supply range of 2.7V to 27V. These features include a chopper-stabilized architecture and an internal bandgap regulator to provide temperature compensated supply for internal circuits. For robustness and protection, the device has built-in reverse blocking diode with a Zener clamp on the supply.

The built-in thermal protection also shuts down the chip if temperature rises to an abnormal value. This will automatically restart the chip once the junction temperature drops below the safe value.

For AH3241Q, AH3242Q, AH3243Q, and AH3244Q 2-wire unipolar switches: when the flux density (south pole) exceeds B_{OP} , the supply current state is turned on (low or high). The output is held until a magnetic flux density falls below B_{RP} , causing output current to be turned off.

For AH3280Q, AH3281Q, and AH3282Q 2-wire latch switches: when the magnetic flux density is larger than B_{OP} , output current is turned on (high). The output state is held until a magnetic flux density reversal falls below B_{RP} , causing output current to be turned off (low).

Features and Performance

- Unipolar: AH3241Q, AH3242Q, AH3243Q, AH3244Q
- Latch: AH3280Q, AH3281Q, AH3282Q
- Output Polarity:
 - Direct: AH3242Q, AH3243Q
 - Inverted: AH3241Q, AH3244Q
- Wide Supply Voltage Operation: 2.7V to 27V
 - Temperature Coefficient -1100ppm/°C
- (AH3242Q, AH3243Q, AH3244Q)
- Chopper Stabilized Design Provides:
 - Superior Temperature Stability
 - Minimal Switch Point Drift
 - Enhanced Immunity to Stress
- Battery polarity reverse connection protection
- Transient Spike Voltage Protection
- Overtemperature Shut Down and Auto-Restart
- UVLO Protection
- High ESD Rating: HBM = 8kV, CDM = 1kV
- Ready for ISO 26262
- Temperature Range: -40°C to +150°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1, 2)
 - Halogen and Antimony Free. "Green" Device (Note 3)

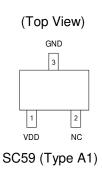
 The AH3241Q-AH3244Q/AH3280Q-AH3282Q

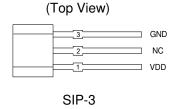
 are suitable for automotive applications requiring specific change control; these parts are AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities. https://www.diodes.com/quality/product-definitions/

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and<1000ppm antimony compounds.

Pin Assignments



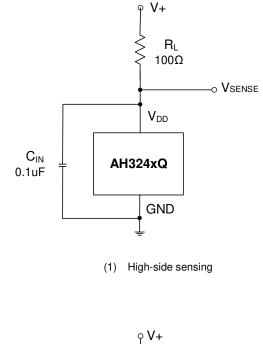


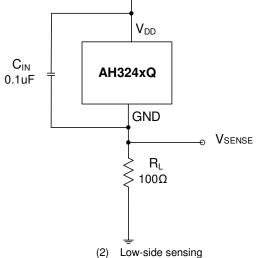
Applications

- Position and proximity sensing in automotive applications
- Seat positioning
- Seatbelt buckles
- Wiper positioning
- Window lifters
- Gear selection positioning



Typical Applications Circuit





Note: 4. A 100nF or larger decoupling capacitor (CIN) between VDD and GND pins is needed for power stabilization and to strengthen noise immunity; CIN needs to be as close to IC as possible. Typical RL value is 100Ω. Larger or additional series resistor is recommended if there are disturbances on VDD.

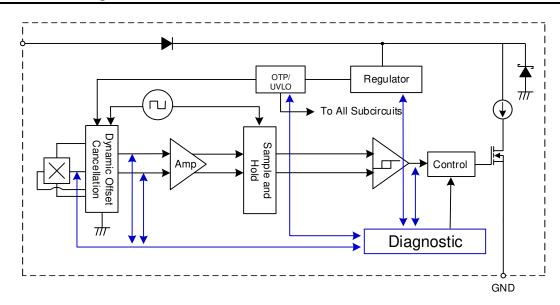
Pin Descriptions

Package: SC59 and SIP-3 (Ammo Pack and Bulk Pack)

Pin Number	Pin Name	Function	
1	V _{DD}	pply voltage input	
2	NC	No connection; can be connected to V _{DD} , GND, or left open.	
3	GND	Ground	



Functional Block Diagram



Absolute Maximum Ratings (Note 5) (@ T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
V _{DD} (Note 6)	Supply Voltage	32	V
V _{DDR} (Note 6) Reverse supply voltage		-32	V
В	Magnetic flux density	Unlimited	Gauss
T_{J_MAX}	Maximum junction temperature	180	°C
Ts	Storage Temperature	-55~180	°C
ESD (HBM)	ESD (Human Body Model)	8000	V
ESD (CDM)	ESD (Charged Device Model)	1000	V

Notes: 5. Stresses greater than the "Absolute Maximum Ratings" specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.

6. Should not be exceeded the maximum junction temperature and maximum duration of 500ms.

Recommended Operating Conditions (@ T_A = -40°C to +150°C, T_J = -40°C to +165°C unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V _{DD}	Supply Voltage, between V_{DD} and GND pins	2.7	27	V
T _{OP}	Operating Ambient Temperature	-40	150	°C



Electrical Characteristics (Note 7) (@ T _A = -40°C to +150°C, T _J = -40°C to +165°C, V _{DD} = 2.7V to 27V, unless otherwise specified)						
	Parameter	Conditions	Min	Тур	Max	Units
V_{DD}	Supply voltage (Note 8)	-	2.7	12	27	V
I _{OFF} (2)	Supply current off state	V _{DD} = 2.7 to 27 V (AH3280Q, AH3282Q)	2	3.3	5	mA
I _{OFF} (1)	Supply current off state	V _{DD} = 2.7 to 27 V (AH3241Q, AH3242Q, AH3243Q, AH3244Q, AH3281Q)	5	6	6.9	mA
I _{ON}	Supply current on state	V _{DD} = 2.7 to 27 V	12	14.5	17	mA
VUVLO	Undervoltage lockout threshold	Voltage dropping	-	2.2	2.7	V
t _{UVLO}	Undervoltage lockout reaction time	-	-	10	-	μs
I _{DDR}	Reverse supply current	$V_{DD} = -18V, T = -40^{\circ}C \text{ to } +150^{\circ}C$	-1.5	-	-	mA
T _{TP}	Thermal protection threshold	Junction temperature	-	190	-	°C
T _{TPR}	Thermal protection release threshold	Junction temperature	-	180	-	°C
F _M	Maximum magnet switching frequency	$B > 3^*B_{OP}$, alternative square magnet field	30	50	-	kHz
Fc	Chopping frequency	-	-	1000	-	kHz
ISAFE	Safe mode supply current	Safe mode supply current / Error Current (mA)	0.5	1	1.5	mA
TPON	Power on delay time (Note 9)	B > Bop+10GS	-	28	40	μs
TD	Response delay time (Note 10)	B > 3*B _{OP}	-	7	-	μs
T _{RF}	Current rise/fall time	V_{DD} = 12V, No bypass capacitor, C_{LOAD} = 50pF to GND	0.1	0.3	1	μs
POS	Power-Up state (Notes 9, 11)	t > T _{PON} (max), V _{DD} slew rate > 1V/µs	-	IOFF	-	-
-	Output jitter	B≥3*B _{OPMAX} 1000 successive square wave switching under 1KHz	-	±3.3	-	μs

7. Typical values are defined at TA = +25°C, VDD = 12V. Maximum and minimum values over the operating temperature range are not tested in production but guaranteed by design, process control and characterization.
8. VDD is the voltage between the VDD pin and the GND pin.
9. When power is initially turned on, V_{DD} must be operated in the correct voltage range to guarantee proper magnetic field sampling, output supply current state level is valid after the start up time of 28µs from V_{DD} higher than 2.7V. Guaranteed by design.
10. Time delayed from the magnetic threshold reached to the output rise or fall. Notes:

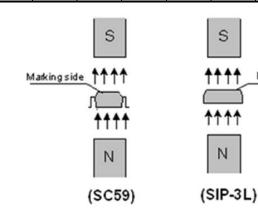
11. t > T_{PON} and $B_{RP} < B < B_{OP}$.

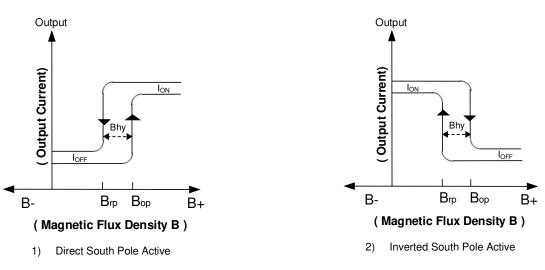


Magnetic Characteristics (Notes 12, 13) ($T_A = -40^{\circ}C$ to $+150^{\circ}C$, $T_J = -40^{\circ}C$ to $+165^{\circ}C$, $V_{DD} = 2.7V$ to 27V, unless otherwise specified)

Part Name	Test Condition		rating Po _{DP} (Gauss			ease Poir P (Gauss)		Temperature Coefficient (ppm/°C)	I _{OFF} (mA)	Active Pole	Output Polarity	
		Min	Тур	Max	Min	Тур	Max	Тур	Тур			
41100410	T _A =25°C	65	90	120	45	70	100	0	0	Cauth	lies contro d	
AH3241Q	T _A =-40~150°C	55	90	135	35	70	115	0	6	South	Inverted	
AH3242Q	T _A =25°C	40	60	80	20	40	60	-1100	6	South	Direct	
AH3242Q	T _A =-40~150°C	30	60	90	10	40	70	-1100	0		Direct	
AH3243Q	T _A =25°C	27	45	63	10	28	46	-1100	1100	C	South	Direct
AH3243Q	T _A =-40~150°C	20	45	70	3	28	53		6	South	Direct	
AH3244Q	T _A =25°C	27	45	63	10	28	46	-1100	6	Couth	Inverted	
AH3244Q	T _A =-40~150°C	20	45	70	3	28	53	-1100	6	South	Inverted	
AH3280Q	T _A =25°C	8	18	28	-28	-18	-8	0		0 3.3	South	Direct
AH320UQ	T _A =-40~150°C	3	18	33	-33	-18	-3	0	3.3	South	Direct	
41100010	T _A =25°C	8	18	28	-28	-18	-8	0	6	Cauth	Divert	
AH3281Q	T _A =-40~150°C	3	18	33	-33	-18	-3	0	6	South	Direct	
AL100000	T _A =25°C	15	30	45	-45	-30	-15	0	0 3.3	Couth	Direct	
AH3282Q	T _A =-40~150°C	10	30	50	-50	-30	-10			South	Direct	

Markingside

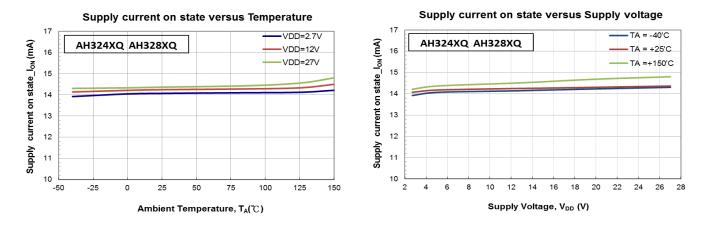




- Notes: 12. Positive x-axis direction indicates the South Pole approaching the part marking surface of SIP3 and SC59 i.e. increasing south pole magnetic field strength to the sensor; reversing direction x-axis toward 0 means the decreasing south magnetic field strength to the sensor. Negative x-axis indicates north pole magnetic field to the part marking surface.
 - 13. Typical values are defined at T_A = +25°C, V_{DD} = 12V. Maximum and minimum values over the operating temperature range is not tested in production but guaranteed by design, process control and characterization.

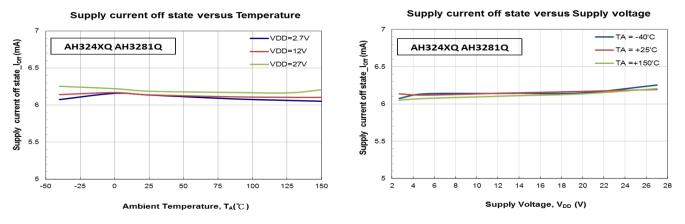


Typical Operating Characteristics



AH324XQ_AH328XQ Supply Current ON, Ion Performance

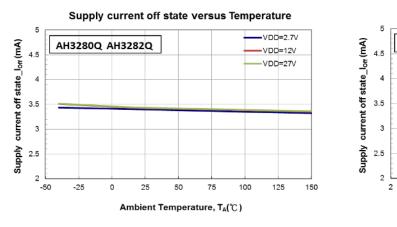
AH324XQ_AH3281Q Supply Current OFF, IOFF(1) Performance





AH3280Q AH3282Q

4 6 8 10 12 14 16 18 20 22 24 26 28



Supply current off state versus Supply voltage

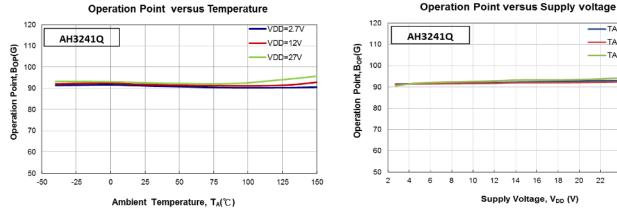
Supply Voltage, V_{DD} (V)

- TA= -40'C

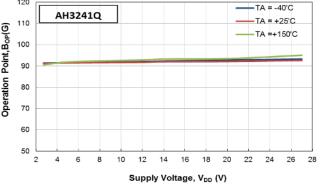
- TA=+25'C

TA=+150'C



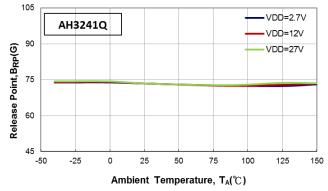


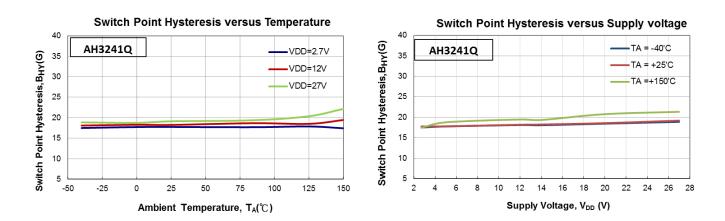
AH3241Q Magnetic Characteristics Performance



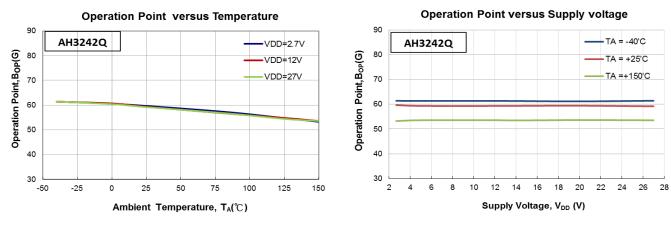
Release Point versus Temperature 105 VDD=2.7V AH3241Q VDD=12V 90 Release Point, B_{RP}(G) VDD=27V 75 60 45 -50 -25 0 25 50 75 100 125 150 Ambient Temperature, T_A (°C)

Release Point versus Temperature

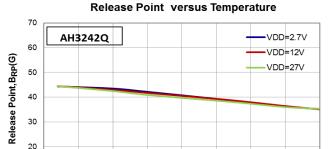








AH3242Q Magnetic Characteristics Performance

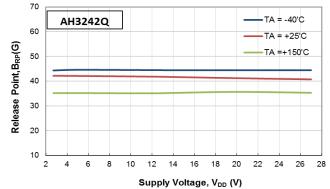


-25 0 25 50 75 100 Ambient Temperature, T_A(°C)

10

-50

Release Point versus Supply voltage

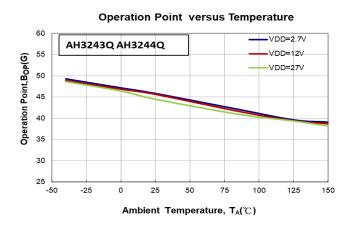


Switch Point Hysteresis versus Temperature Switch Point Hysteresis versus Supply voltage 40 40 Switch Point Hysteresis, B_{HY}(G) Switch Point Hysteresis, B_{HY}(G) AH3242Q AH3242Q VDD=2.7V -TA = -40'C 35 35 -TA = +25'C VDD=12V 30 30 -TA =+150'C VDD=27V 25 25 20 20 15 15 10 10 5 5 4 6 8 10 12 14 16 18 20 22 24 26 28 -50 -25 0 25 50 75 100 125 150 2 Supply Voltage, V_{DD} (V) Ambient Temperature, T_A(℃)

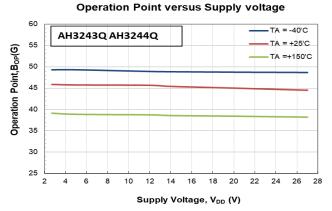
125

150



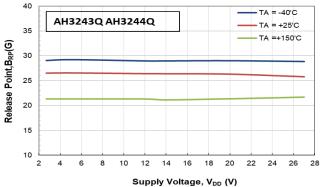


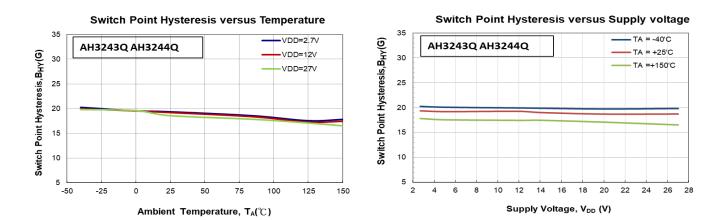
AH3243Q_AH3244Q Magnetic Characteristics Performance



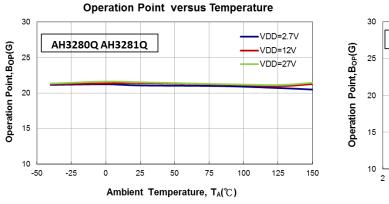
Release Point versus Temperature 40 VDD=2.7V AH3243Q AH3244Q VDD=12V 35 VDD=27V Release Point, BRP(G) 30 25 20 15 10 -50 -25 0 25 50 75 100 125 150 Ambient Temperature, T_A (°C)

Release Point versus Supply voltage

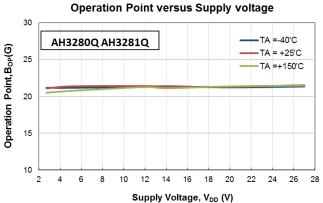






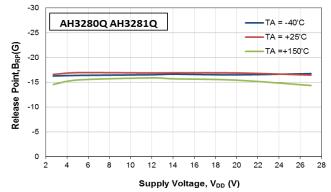


AH3280Q_AH3281Q Magnetic Characteristics Performance

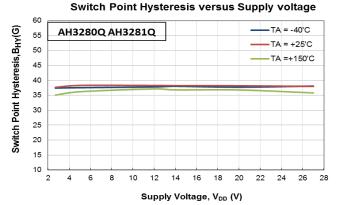


Release Point versus Temperature -30 VDD=2.7V AH3280Q AH3281Q VDD=12V -25 VDD=27V Release Point, BRP(G) -20 -15 -10 -5 0 -50 -25 Ó 25 50 75 100 125 150 Ambient Temperature, T_A(℃)

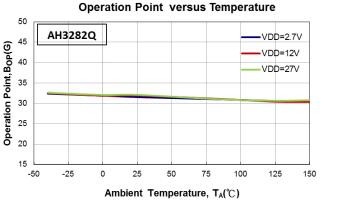
Release Point versus Supply voltage



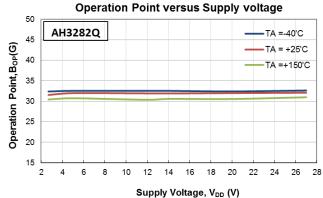
Switch Point Hysteresis versus Temperature 60 VDD=2.7V AH3280Q AH3281Q Switch Point Hysteresis, B_HY(G) 55 VDD=12V 50 VDD=27V 45 40 35 30 25 20 15 10 -50 -25 0 25 50 75 100 125 150 Ambient Temperature, T_A(℃)

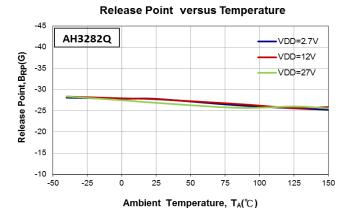




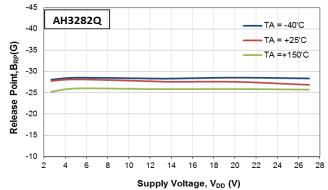


AH3282Q Magnetic Characteristics Performance





Release Point versus Supply voltage



Switch Point Hysteresis versus Temperature Switch Point Hysteresis versus Temperature 90 90 Switch Point Hysteresis, B_{HY}(G) Switch Point Hysteresis, B_{HY}(G) AH3282Q AH3282Q VDD=2.7V 80 80 VDD=12V VDD=12V VDD=27V 70 70 60 60 50 50 40 40 30 30 -50 -25 0 25 50 75 100 -50 -25 0 25 50 75 100 125 150 Ambient Temperature, T_A(°C) Ambient Temperature, T_A(℃)

VDD=2.7V

VDD=27V

125

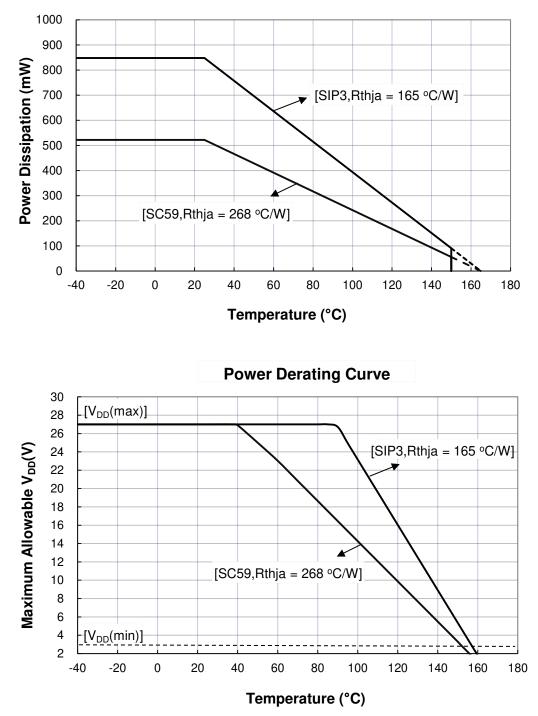
150



Thermal Performance Characteristics

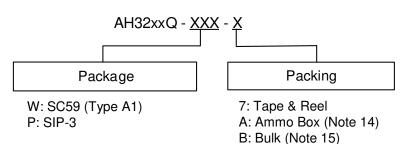
Symbol	Parameter	Conditions	Rating	Unit
R _{0 JA} Package Thermal Resistance	SC59, 50mm*50mm 2oz MRB PCB, single layer	268	°C/W	
	SIP-3, 50mm*50mm 2oz MRB PCB, single layer	143	°C/W	

Thermal Derating Curve vs. Ambient Temperature





Ordering Information



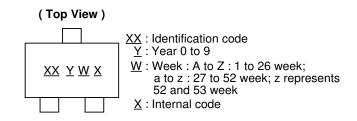
	Package		Bul	lk Box	7" Tape and Reel		Ammo Box	
Part Number	Code	Packaging	Quantity	Part Number Suffix	Quantity	Part Number Suffix	Quantity	Part Number Suffix
AH3241Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3241Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3241Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3242Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3242Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3242Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3243Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3243Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3243Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3244Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3244Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3244Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3280Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3280Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3280Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3281Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3281Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3281Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA
AH3282Q-P-A	Р	SIP-3 (Ammo Pack)	NA	NA	NA	NA	4000/Box	-A
AH3282Q-P-B	Р	SIP-3 (Bulk Pack)	1000	-В	NA	NA	NA	NA
AH3282Q-W-7	W	SC59 (Type A1)	NA	NA	3000/Tape & Reel	-7	NA	NA

14. Ammo Box is for SIP-3 (Ammo Pack) Spread Lead. 15. Bulk is for SIP-3 (Bulk Pack) Straight Lead. Notes:



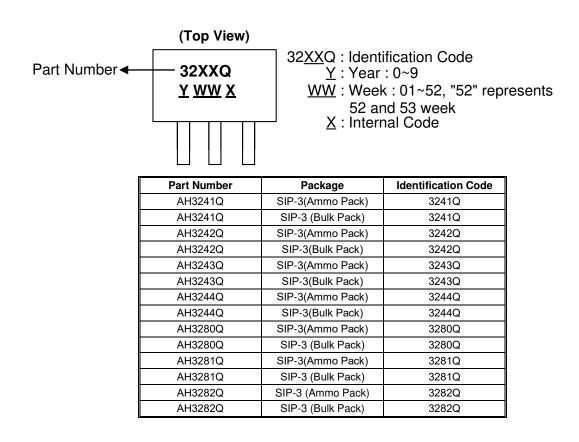
Marking Information

(1) Package Type: SC59 (Type-A1)



Part Number	Package	Identification Code
AH3241Q	SC59 (Type A1)	BR
AH3242Q	SC59 (Type A1)	BS
AH3243Q	SC59 (Type A1)	BT
AH3244Q	SC59 (Type A1)	BX
AH3280Q	SC59 (Type A1)	BW
AH3281Q	SC59 (Type A1)	BU
AH3282Q	SC59 (Type A1)	BV

(2) Package Type: SIP-3 (Ammo Pack), SIP-3 (Bulk Pack)

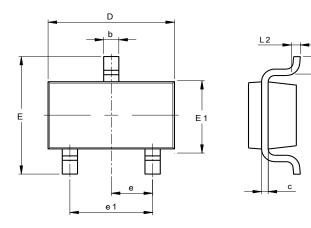


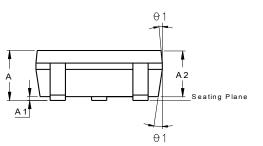


Package Outline Dimensions (All dimensions in mm.)

Please see http://www.diodes.com/package-outlines.html for the latest version.

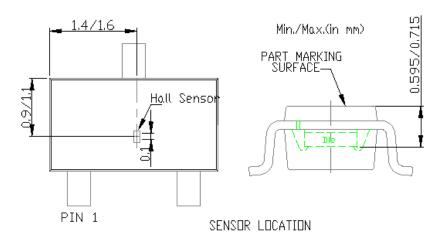
(1) Package Type: SC59 (Type A1)





	0050 /	-			
		Туре /	· ·		
Dim	Min				
Α		1.45			
A1	0.00	0.15			
A2	0.90	1.15			
b	0.30	0.30 0.50			
С	0.08	0.22			
D	2.90 BSC				
E		2.80 B	SC		
E1		1.60 B	SC		
е		0.95 B	SC		
e1		1.90 B	SC		
L	0.30	0.60	0.45		
L2	0.25 BSC				
θ1	5°	15°	10°		
	Dimen	sions i	in mm		

AH32xxQ Hall sensor

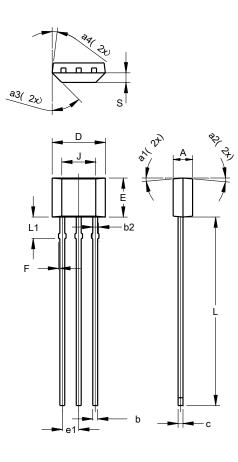




Package Outline Dimensions (continued) (All dimensions in mm.)

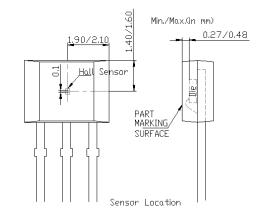
Please see http://www.diodes.com/package-outlines.html for the latest version.

(2) Package Type: SIP-3 (Bulk Pack)



S	IP-3 (Bu	Ik Pack	()	
Dim	Min	Max	Тур	
Α	1.40	1.60	1.50	
b	0.33	0.43	0.38	
b2	0.40	0.508	0.46	
С	0.35	0.41	0.38	
D	3.90	3.90 4.30 4.1		
E	2.80 3.20 3.0			
e1	1.24	1.24 1.30		
F	0.00 0.20 -			
J	2	.62 REF	-	
L	14.00	15.00	14.50	
L1	1.55	1.75	1.65	
S	0.63	0.84	0.74	
a1	—		5°	
a2	_		5°	
a3	_	_	45°	
a4	_	_	3°	
All [Dimensi	ons in	mm	

AH32xxQ SIP3 Hall sensor

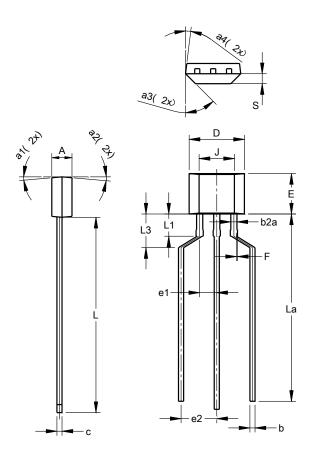




Package Outline Dimensions (continued) (All dimensions in mm.)

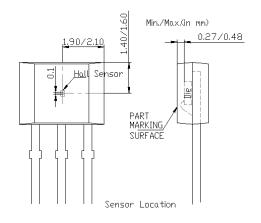
Please see http://www.diodes.com/package-outlines.html for the latest version.

(3) Package Type: SIP-3 (Ammo Pack)



SIP-3				
	(Ammo	-		
Dim	Min	Max	Тур	
Α	1.40	1.60	1.50	
b	0.33	0.43	0.38	
b2a	0.40	0.52	0.46	
С	0.35	0.41	0.38	
D	3.90	4.30	4.10	
E	2.80	3.20	3.00	
e1	1.24	1.27		
e2	2.40	2.90	2.65	
F	0.00	0.20	—	
J		.62 REF		
L	14.00	15.00	14.50	
La	12.90	14.90	13.90	
L1	1.55	1.75	1.65	
L3	2.00	3.00	2.50	
S	0.63	0.84	0.74	
a1	—	_	5°	
a2	—	_	5°	
a3	—	_	45°	
a4	—	_	3°	
All I	Dimensi	ons in	mm	

AH32xxQ SIP3 Hall sensor



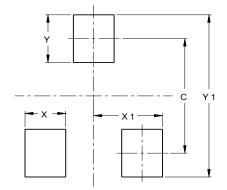
AH3241Q-AH3244Q/AH3280Q-AH3282Q Document number: DS41822 Rev. 5 - 2



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SC59 (Type A1)



Dimensions	Value (in mm)
С	2.40
Х	0.80
X1	1.35
Y	1.00
Y1	3.40



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